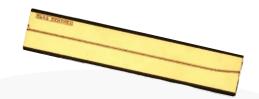
High Power RSOA Chip



Part Number: CHP-289

High Power RSOA Chip Single-Mode RSOA Fabry-Perot Wavelength at 1310nm



Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard ROSA Bare Die
- Cost Effective

Application

- OTDR
- LiDAR
- Free Space Communications
- Network Test Equipment



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars, and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

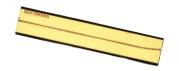
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High Power RSOA Chip



Specification

CHP-289



Optical	Symbol	Тур.	Units
Center Wavelength	λ_{C}	1310	nm
Aperture Width	AW	4	μm
Aperture Height	AH	1	μm
Beam Exit Angle	θεхτ	19.5	Degree
Noise Figure	NF	6	dB
Polarization Extinction Ratio	PER	18	dB
Fast Axis Div.	Θ⊥	28	Deg FWHM
Slow Axis Div.	Θ	16	Deg FWHM
Front Facet Reflectivity		<0.1%	
Rear Face Reflectivity		98%	
Waveguide		Curved	
Electrical	Symbol		Units
Operating Current	l _{op}	1	А
Operating Voltage	V _{op}	2	V
Mechanical		Range	Units
Chip Length		2500	μm
Chip Width		500	μm
Operating Temp.**		-20 to 75	°C
Storage Temp.		-40 to 85	°C

Specified values are rated at a constant heat sink temperature of 20°C.

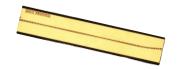
**High temperature operation will reduce performance and MTTF.

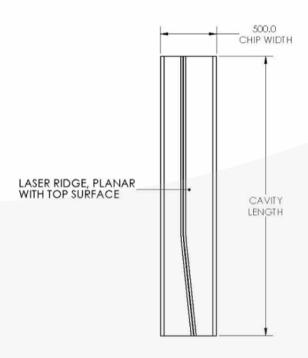
Unless otherwise indicated all values are nominal.

High Power RSOA Chip



Mechanical Drawing





CHIP ATTRIBUTES			
WAVELENGTH	1550nm ±20nm		
APERTURE WIDTH	4μm ±1μm		
CHIP WIDTH	0.500mm ±10µm		
THICKNESS	160µm±10µm		
CAVITY LENGTH	2.5mm ±10µm		

P-METAL				
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)		
Ti	50	±10		
Pt	125	±25		
Αu	250	±50		

N-METAL				
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)		
Ti	30	±10		
Pt	125	±25		
Αu	400	±40		

0.0 P-SIDE FULLY METALIZED SURFACE

160.0 N-SIDE FULLY METALIZED SURFACE

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